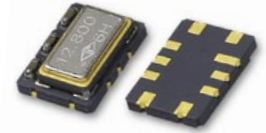


TS Type Stratum III Voltage Controlled Temperature Compensated Crystal Oscillator

RoHS Compliant Standard

FEATURE

1. Typical 7.0 x 5.0 x 2.0 mm ceramic SMD package.
2. Stratum 3 (Overall ± 4.6 ppm including 20 years aging)
3. CMOS and Clipped Sine wave (without DC-cut capacitor) output optional.
4. Packing: Tape & Reel 1000/3000 pcs per Reel.



Actual Size



ORDERING INFORMATION

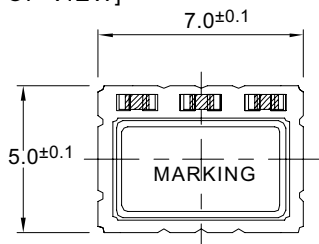
T	S	E	A	T	L	J	A	N	F	-	?
TCXO	Package (mm)	Supply Voltage (V)	Pulling Range (ppm)	Freq. Stability (ppm)	Temp. Range (°C)	Output Logic and Symmetry	Oscillator Mode	Appearance	Lead Free	Dash	Freq. (MHz)
	S: 7.0 x 5.0 x 2.0	C: 5V E: 3.3V	A: ± 5 B: ± 8 T: TCXO	T: ± 4.6 (Including 20 Years Aging)	C: -20~+70 L: -40~+85	50 \pm 5% CMOS 15pF S: Clipped Sine Wave	-A: AT Fundamental * Not Selectable by Customer	N: Normal	F: RoHS Compliant		XX.XXXXXX

Ordering Example: TSEATLJANF-12.800000 MHz

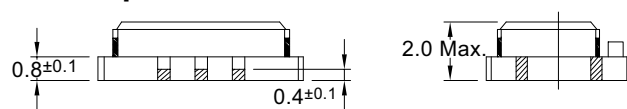
TCXO S-TYPE; V_{DD}: 3.3V; Pulling Range: ± 5 ppm; Freq. Stability: ± 4.6 (Including 20 Years Aging); Temp. Range: -40°C to +85°C; Load: CMOS 15pF, Symmetry: 50 \pm 5%; AT Fundamental; Normal Appearance; RoHS Compliant; Freq.: 12.800000 MHz.

OUTLINE DRAWING

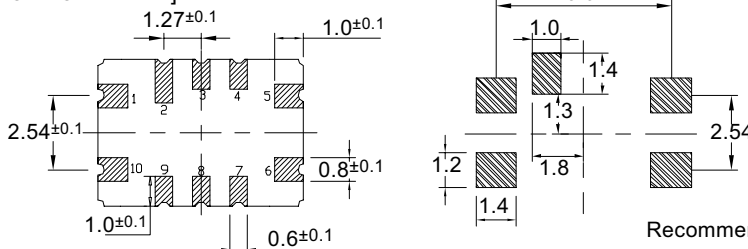
[TOP VIEW]



[SIDE VIEW]



[BOTTOM VIEW]



Recommended Soldering Pattern

Pad	Function
1	VCON : VC-TCXO NC : TCXO
2	NC
3	NC
4	NC
5	GND
6	CMOS/ Clipped Sinewave Output
7	NC
8	NC
9	Tri-State Control*
10	V _{DD}

*Tri-state:

1. Pad 9 > 70%V_{DD} or NC: Output Enable
2. Pad 9 < 30%V_{DD} or NC: Output Enable

VCTCXO / TCXO

ELECTRICAL SPECIFICATION

Parameter	Min.		Max.		Unit
	5.0	3.3	5.0	3.3	
Supply Voltage Variation(V_{DD}) 5%	4.75	3.13	5.25	3.47	V
Frequency Range	10		26		MHz
Standard Frequency (for CMOS)	12.800				
Standard Frequency (for Clipped sine)	10.00, 12.80, 19.20, 19.44, 25.60				
Operating Temp. Range	Refer to Ordering Information				°C
Frequency Stability (Overall)	±4.6				ppm
Frequency Stability					ppm
Vs Temperature Range (@-20°C ~ +70°C)	-		±0.28		
Vs Temperature Range (@-40°C ~ +85°C)	-		±0.37		
Supply Current (CMOS output)	-		6		mA
Supply Current (Clipped Sine-wave output)	-		3.5		
Output Level (CMOS)					V
Output High (Logic "1")	90% V _{DD}		-		
Output Low (Logic "0")	-		10% V _{DD}		
Duty	45%		55%		%
Output Level (Clipped Sine Wave)	0.8		-		V _{p-p}
V_c Input Impedance	100		-		KΩ
Phase Noise @12.8MHz					dBc/Hz
100Hz			-120		
1KHz			-140		
10KHz			-148		
Start Time	-		2		mSec
Tri-state					V
Disable	-		(V _{DD})*20%		
Enable	(V _{DD})*80%		-		
Storage Temp. Range	-55		125		°C